

## Features

- AEC-Q101 Qualified
- Complementary Pari: NPN(3904), PNP(3906)
- Ideal for Low Power Amplification and Switching
- Epitaxial Planar Die Construction
- Halogen Free. "Green" Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## Maximum Ratings @ 25°C Unless Otherwise Specified

- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C

### NPN Transistor

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Continuous Collector Current	$I_C$	200	mA
Power Dissipation	$P_D$	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W

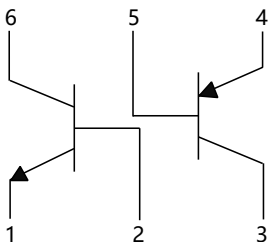
### PNP Transistor

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-40	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Continuous Collector Current	$I_C$	-200	mA
Power Dissipation	$P_D$	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W

Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

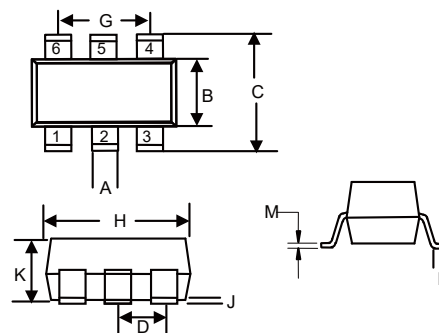
## Marking: K46

## Internal Structure



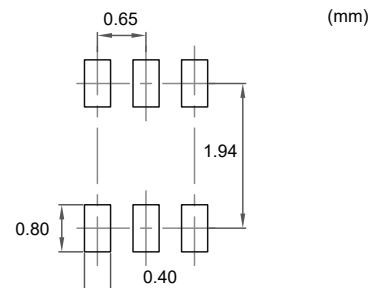
# NPN/PNP Small Signal Surface Mount Transistors

## SOT-363



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	0.006	0.014	0.15	0.35	
B	0.045	0.053	1.15	1.35	
C	0.079	0.096	2.00	2.45	
D			0.65		TYP.
G	0.047	0.055	1.20	1.40	
H	0.071	0.087	1.80	2.20	
J	-----	0.004	-----	0.10	
K	0.031	0.043	0.80	1.10	
L	0.010	0.018	0.26	0.46	
M	0.003	0.006	0.08	0.15	

## Suggested Solder Pad Layout



**Electrical Characteristics @  $T_A=25^\circ\text{C}$  Unless Otherwise Specified**
**NPN Transistor**

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60			V	$I_C=10\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40			V	$I_C=1\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6			V	$I_E=10\mu\text{A}, I_C=0$
Collector Cutoff Current	$I_{CBO}$			50	nA	$V_{CB}=30\text{V}, I_E=0$
Collector Cutoff Current	$I_{CEO}$			500	nA	$V_{CE}=30\text{V}, I_B=0$
Emitter Cutoff Current	$I_{EBO}$			50	nA	$V_{EB}=5\text{V}, I_C=0$
DC Current Gain	$h_{FE(1)}$	40				$V_{CE}=1\text{V}, I_C=0.1\text{mA}$
	$h_{FE(2)}$	70				$V_{CE}=1\text{V}, I_C=1\text{mA}$
	$h_{FE(3)}$	100		300		$V_{CE}=1\text{V}, I_C=10\text{mA}$
	$h_{FE(4)}$	60				$V_{CE}=1\text{V}, I_C=50\text{mA}$
	$h_{FE(5)}$	30				$V_{CE}=1\text{V}, I_C=100\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.2	V	$I_C=10\text{mA}, I_B=1\text{mA}$
				0.3	V	$I_C=50\text{mA}, I_B=5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	0.65		0.85	V	$I_C=10\text{mA}, I_B=1\text{mA}$
				0.95	V	$I_C=50\text{mA}, I_B=5\text{mA}$
Transition Frequency	$f_T$	300			MHz	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$
Delay Time	$t_d$			35	ns	$V_{CC}=3\text{V}, I_C=10\text{mA}, V_{BE}=0.5\text{V}, I_{B1}=1\text{mA}$
Rise Time	$t_r$			35	ns	
Storage Time	$t_s$			200	ns	$V_{CC}=3\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1\text{mA}$
Fall Time	$t_f$			50	ns	
Output Capacitance	$C_{ob}$			4	pF	$V_{CB}=5\text{V}, I_E=0, f=1\text{MHz}$
Noise Figure	$N_F$			5	dB	$V_{CE}=5\text{V}, I_C=0.1\text{mA}, f=1\text{KHz}, R_s=1\text{K}\Omega$

**Electrical Characteristics @  $T_A=25^\circ\text{C}$  Unless Otherwise Specified**
**PNP Transistor**

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40			V	$I_C=-10\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40			V	$I_C=-1\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E=-10\mu\text{A}, I_C=0$
Collector Cutoff Current	$I_{CBO}$			-50	nA	$V_{CB}=-30\text{V}, I_E=0$
Emitter Cutoff Current	$I_{EBO}$			-50	nA	$V_{EB}=-5\text{V}, I_C=0$
DC Current Gain	$h_{FE(1)}$	40				$V_{CE}=-1\text{V}, I_C=-0.1\text{mA}$
	$h_{FE(2)}$	70				$V_{CE}=-1\text{V}, I_C=-1\text{mA}$
	$h_{FE(3)}$	100		300		$V_{CE}=-1\text{V}, I_C=-10\text{mA}$
	$h_{FE(4)}$	60				$V_{CE}=-1\text{V}, I_C=-50\text{mA}$
	$h_{FE(5)}$	30				$V_{CE}=-1\text{V}, I_C=-100\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.25	V	$I_C=-10\text{mA}, I_B=-1\text{mA}$
				-0.4	V	$I_C=-50\text{mA}, I_B=-5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.65		-0.85	V	$I_C=-10\text{mA}, I_B=-1\text{mA}$
				-0.95	V	$I_C=-50\text{mA}, I_B=-5\text{mA}$
Transition Frequency	$f_T$	250			MHz	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$
Delay Time	$t_d$			35	ns	$V_{CC}=-3\text{V}, I_C=-10\text{mA}, V_{BE}=-0.5\text{V}, I_{B1}=-I_{B2}=-1\text{mA}$
Rise Time	$t_r$			35	ns	
Storage Time	$t_s$			225	ns	$V_{CC}=-3\text{V}, I_C=-10\text{mA}, I_{B1}=-I_{B2}=-1\text{mA}$
Fall Time	$t_f$			75	ns	
Output Capacitance	$C_{ob}$			4.5	pF	$V_{CB}=-5\text{V}, I_E=0, f=1\text{MHz}$
Noise Figure	$N_F$			4	dB	$V_{CE}=-5\text{V}, I_C=-0.1\text{mA}, f=1\text{KHz}, R_s=1\text{K}\Omega$

**Curve Characteristics(NPN)**

Fig. 1 - Static Characteristics

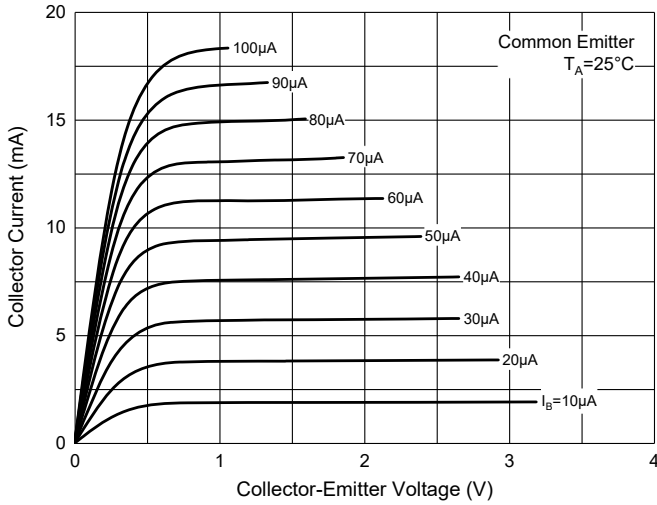


Fig. 2 - DC Current Gain Characteristics

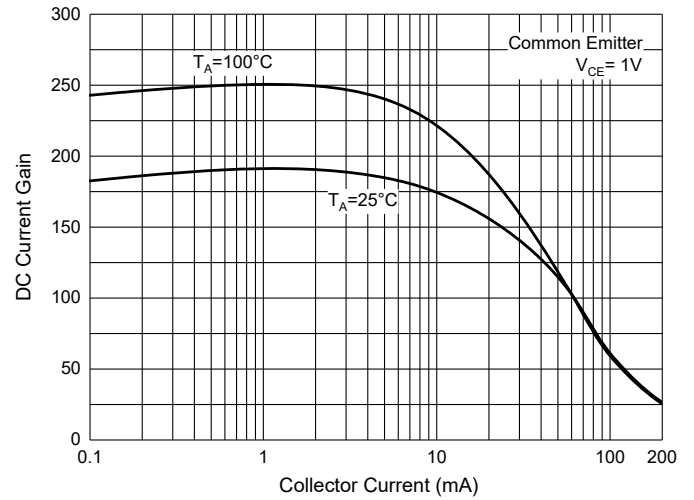


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

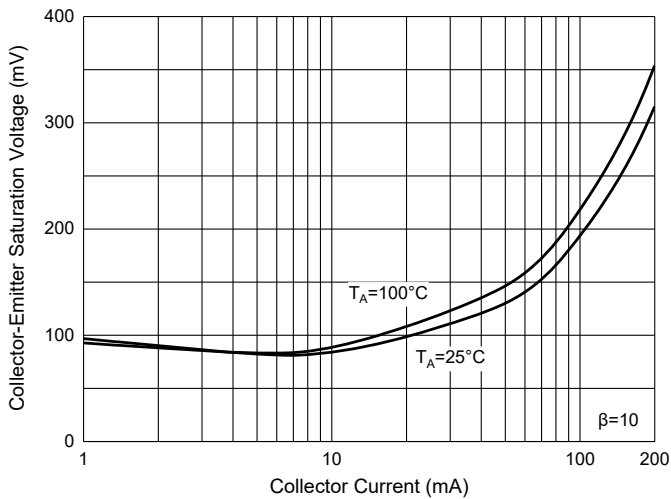


Fig. 4 - Base-Emitter Saturation Voltage Characteristics

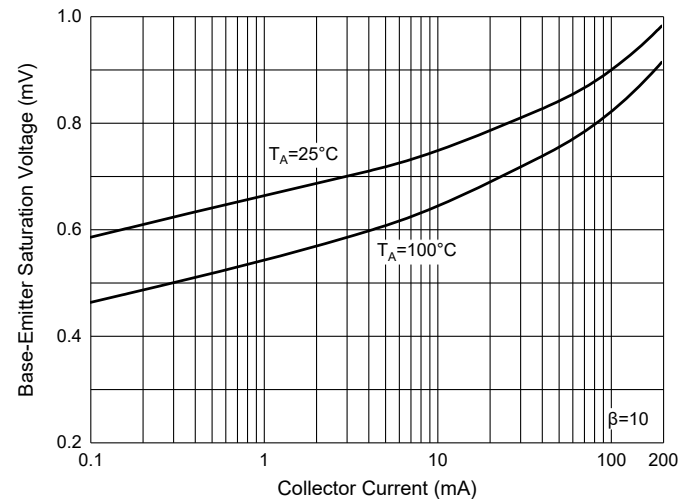


Fig. 5 - Base-Emitter Voltage Characteristics

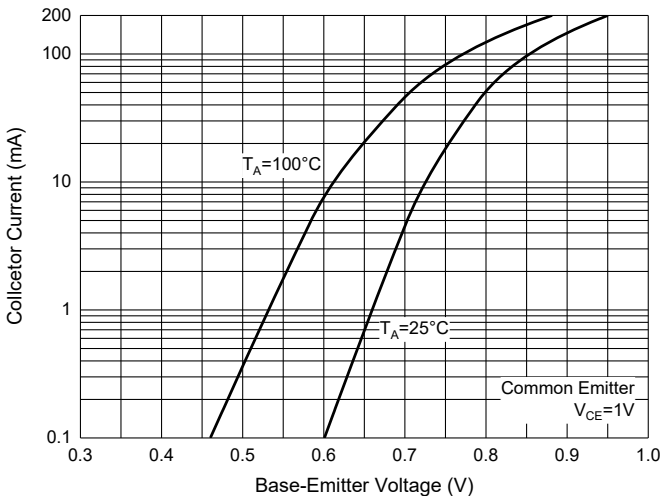
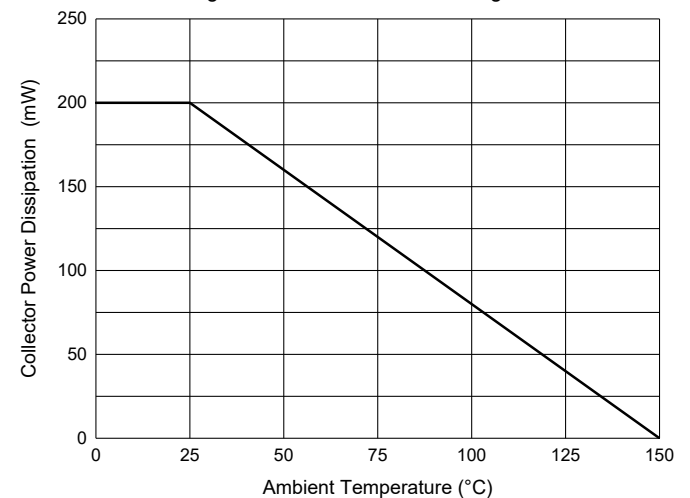


Fig. 6 - Collector Power Derating Curve



**Curve Characteristics(PNP)**

Fig. 7 - Static Characteristics

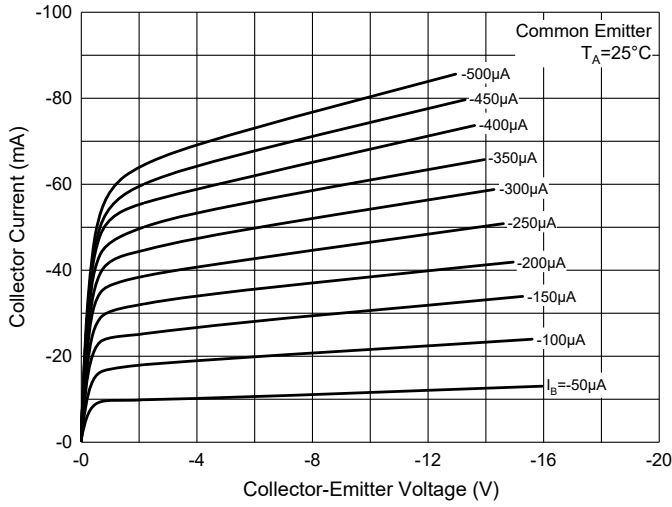


Fig. 8 - DC Current Gain Characteristics

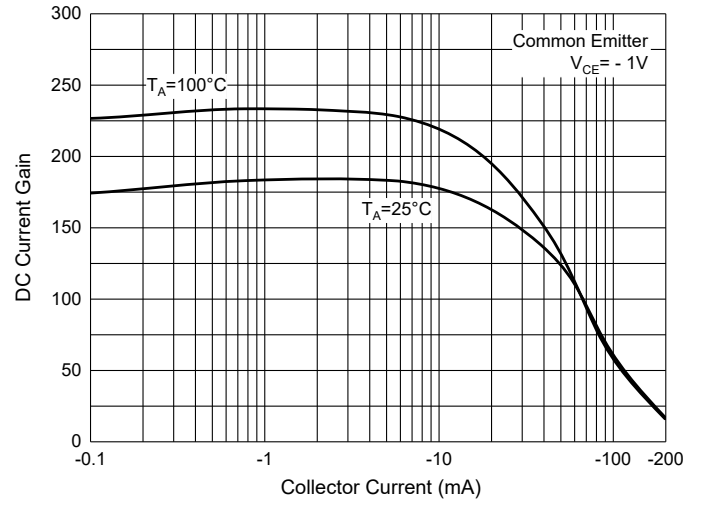


Fig. 9 - Collector-Emitter Saturation Voltage Characteristics

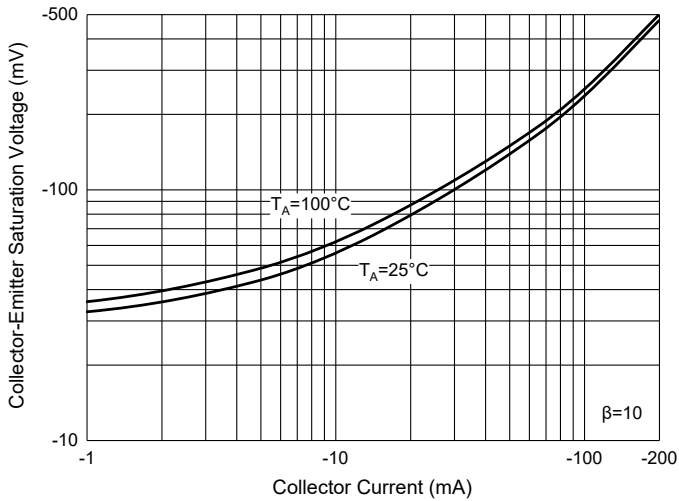


Fig. 10 - Base-Emitter Saturation Voltage Characteristics

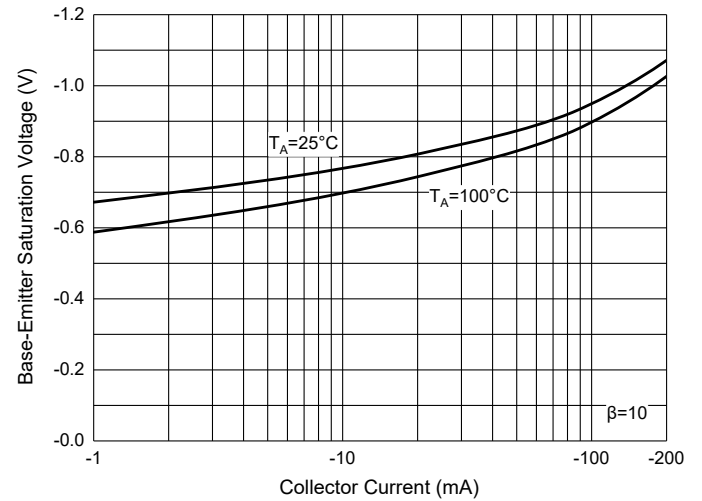


Fig. 11 - Base-Emitter Voltage Characteristics

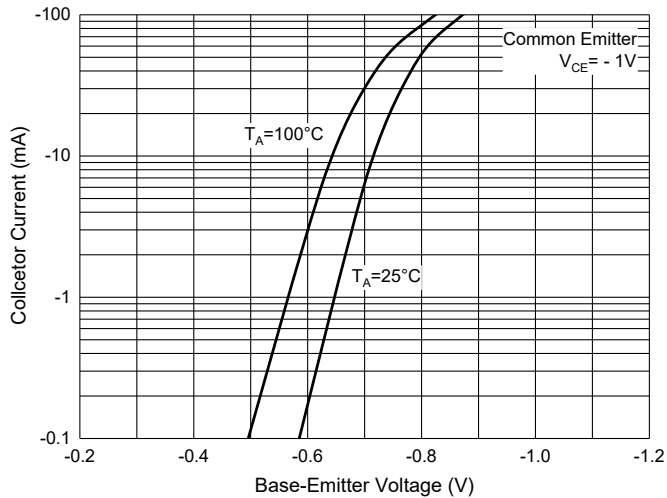
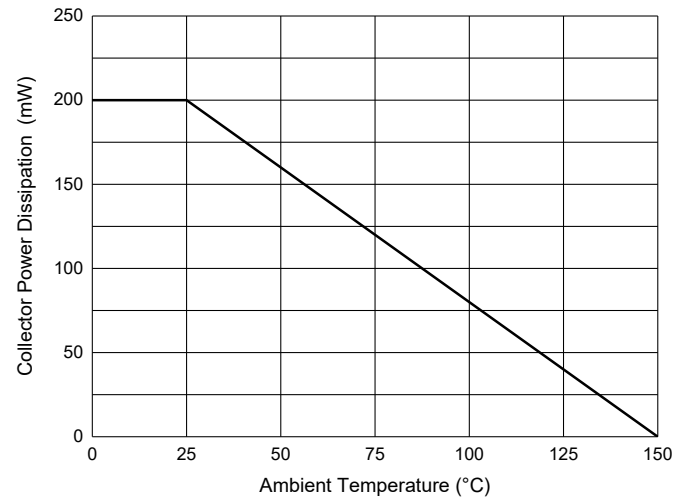


Fig. 12 - Collector Power Derating Curve



## Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel

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